

Notice of References Cited	Application No. 10/635,574	Applicant(s) Kaneko et al	
	Examiner M.L. Padgett	Group Art Unit 1762	Page 1 of 1

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B	5,475,071	12/1995	Smart et al	526	247
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X N	WO 02/065212A1	Aug 22, 2002	PCT	(Applicants) Kaneko et al		
O	WO 00/17712	March 2000	PCT	Feiring		
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V	Ito et al, "Polymer design for 157nm chemically amplified resins"; F. Houlihan, ed, <u>Advances in Resist Tech. & Processing XVII</u> , <u>Proceeding of SPIE</u> , Vol. 4345, p. 273-284	Feb 2001
W	Toriumi et al, "Fluoropolymer based resist for a single-resist process of 157nm Lithography"; <u>J. Vac. Sci. Technol. B</u> , 20(6), p. 2909-2912	Nov/Dec 2002
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* A copy of this reference is not being furnished with this Office action.
(See Manual of Patent Examining Procedure, Section 707.05(a).)